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(54) SEMICONDUCTOR STORAGE DEVICE

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(57) Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor storage device which can reduce the size of a memory cell and realize high integration.

SOLUTION: A drive transistor Qn1 and a word transistor Qn3 are formed on a p-type active region 11a. Similarly, a drive transistor Qn2 and a word transistor Qn4 are formed on a p-type active region 11b. A word line (WL) 14 is arranged nearly perpendicular to both of the two p-type active regions 11a and 11b. A pMOS load transistor Qp1 is formed on an n-type active region 12a, and a load transistor Qp2 is formed on an n-type active region 12b. A length DTw of the drive transistor is longer than a length LTW of the load transistor. Thereby a cell area can be made smaller than that of prior art SRAM cell, while obtaining the same cell current and the same SNM.

